

# DMP6350S-7 Datasheet



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DiGi Electronics Part Number DMP6350S-7-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMP6350S-7

Description MOSFET P-CH 60V 1.5A SOT23

Detailed Description P-Channel 60 V 1.5A (Ta) 720mW (Ta) Surface Mou

nt SOT-23-3



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
DMP6350S-7	Diodes Incorporated
Series:	Product Status:
	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
60 V	1.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	350mOhm @ 900mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250μA	4.1 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	206 pF @ 30 V
FET Feature:	Power Dissipation (Max):
	720mW (Ta)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
SOT-23-3	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
DMP6350	

## **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





#### **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
2014	$350\text{m}\Omega$ @ $V_{GS} = -10V$	-1.5A
-60V	550mΩ @ V <sub>GS</sub> = -4.5V	-1.2A

#### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

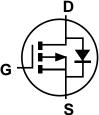
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

#### **Mechanical Data**

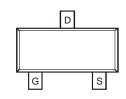
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 (63)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)







Internal Schematic



Top View

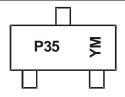
#### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP6350S-7	SOT23	3,000/Tape & Reel
DMP6350S-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



P35 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y}= Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Bate Code Hoy								
Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	С	D	E	F	G	Н	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



#### Maximum Ratings (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	-60	V	
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6), V <sub>GS</sub> = -10V	I <sub>D</sub>	-1.5 -1.2	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I <sub>DM</sub>	-6	А	

#### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.72	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	176	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	1.17	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>θJA</sub>	108	°C/W
Thermal Resistance, Junction to Case	R <sub>eJC</sub>	34	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

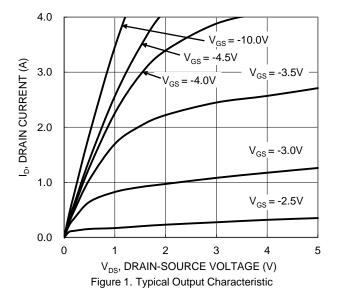
#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

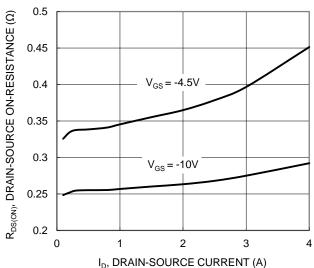
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	-1.0	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-1.8	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance			257	350	mΩ	$V_{GS} = -10V, I_D = -0.9A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	343	550	11122	$V_{GS} = -4.5V, I_D = -0.8A$	
Diode Forward Voltage	$V_{SD}$	-	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	-	206	-	pF		
Output Capacitance	Coss	-	15	-	pF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	11	-	рF	1 = 1.000112	
Gate Resistance	$R_{g}$	-	17	-	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	-	2.0	-	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	-	4.1	-	nC	201/ 1 0.04	
Gate-Source Charge	$Q_{gs}$	-	0.5	-	nC	$V_{DS} = -30V, I_{D} = -0.9A$	
Gate-Drain Charge	$Q_{gd}$	-	0.8	-	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	3.6	-	ns		
Turn-On Rise Time	t <sub>R</sub>	-	3.8	-	ns	$V_{DD} = -30V, V_{GS} = -10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	12.3	-	ns	$I_D = -1.0A$ , $R_q = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	-	7.3	-	ns	7	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	8.2	-	ns	I <sub>S</sub> = -1.0A, di/dt = -100A/μs	
Body Diode Reverse Recovery Charge	$Q_{RR}$	-	2.7	-	nC	$I_S = -1.0A$ , di/dt = -100A/ $\mu$ s	

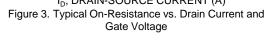
Notes:

- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.









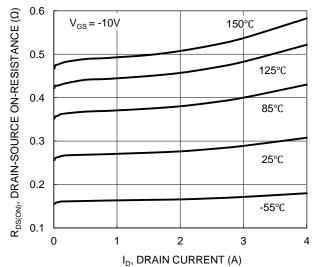
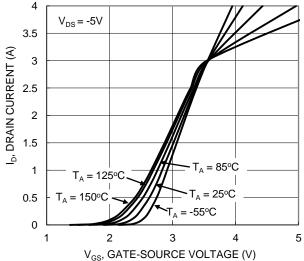


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

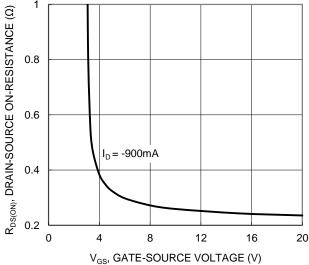


Figure 4. Typical Transfer Characteristic

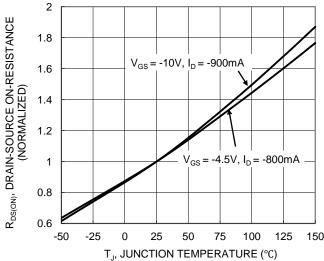


Figure 6. On-Resistance Variation with Junction Temperature



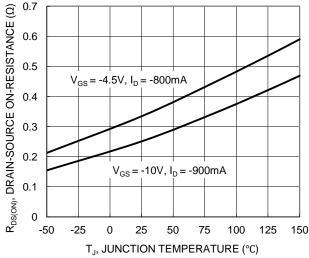


Figure 7. On-Resistance Variation with Junction Temperature

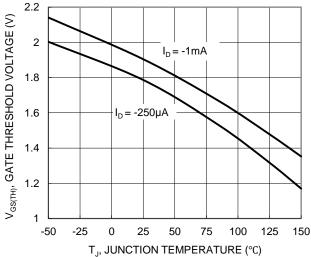
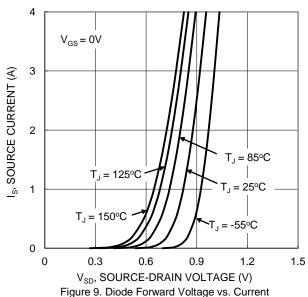
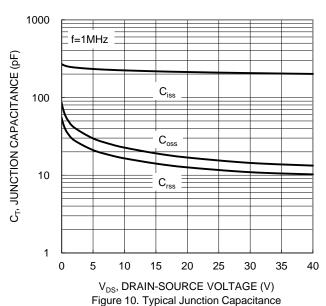
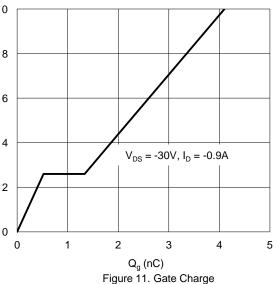


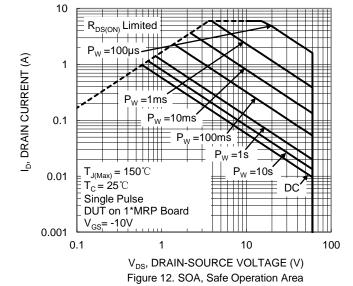
Figure 8. Gate Threshold Variation vs. Junction Temperature



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 $V_{GS}(V)$ 



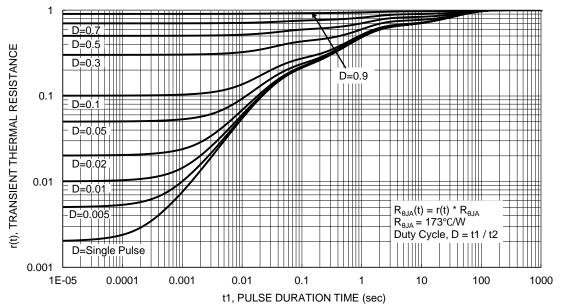


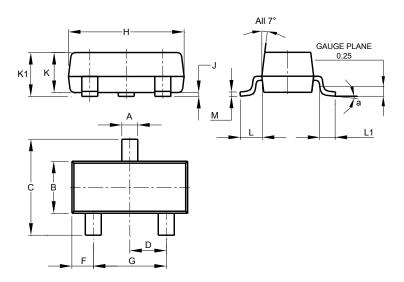
Figure 13. Transient Thermal Resistance



#### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

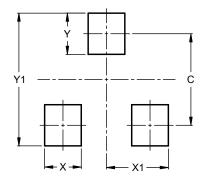


		SOT2	3					
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
M	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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